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Sheet 1 of 1

FORM PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY.DOCKET NO. 06425ZP	SERIAL NO. 10/784,377 AC
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	APPLICANT Richard Van Court Carr, et al..	
(37 CFR 1.98(b))	FILING DATE	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RVC	2003	0 0 5 9 7 1 0	3/27/2003	Inoue	430	270.1	
RVC	2002	0 0 0 4 5 7 0	1/10/2002	A. Zampini, et al.	526	257	2/23/2001
RVC	2002	0 0 5 1 9 3 6	5/2/2002	Y. Harada, et al.	430	270.1	9/7/2001
RVC	2002	0 0 5 5 5 0 6 0	5/9/2002	G. N. Taylor, et al.	430	270.1	9/8/2001
RVC	2002	0 0 6 1 4 6 4	5/23/2002	T. Acai, et al.	430	270.1	9/25/2001
RVC		6 2 9 1 1 3 0	9/18/2001	K. Kodama, et al.	430	270.1	7/27/1999
RVC		6 4 0 6 8 2 8	6/18/2002	C. R. Szmanda, et al.	430	270.1	2/24/2000

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
RVC	JP	2 1 7 9 7 3 1	7/2002	Japan (Abstract)			X	
RVC	WO	0 2 3 1 5 9 5	4/2002	World	G03F	7/00	X	
RVC	EP	1 1 0 3 8 5 6	3/2001	Europe	G03F	7/039	X	
RVC	EP	1 1 2 6 3 2 2	8/2002	Europe	G03F	7/039	X	
RVC	WO	0 0 1 7 7 1 2	3/2000	World	G03F	7/039	X	
RVC	WO	0 0 6 7 0 7 2	11/2000	World	G03F	7/004	X	
RVC	WO	0 1 6 3 3 6 2	8/2001	World	G03F	7/00	X	
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RVC	WO	0 2 2 1 2 1 3	3/2002	World	G03F	7/004	X	
RVC	WO	0 2 2 1 2 1 4	3/2002	World	G03F	7/004	X	
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		RVC	Hiroshi Ito, et al., "Synthesis and Evaluation of Alicyclic Backbone Polymers for 193 nm Lithography", American Chemical Society, 1998.
		RVC	Hiroshi Ito, et al., "Aliphatic Platforms for the Design of 157 nm Chemically Amplified Resists", SPIE Proceedings, Vol. 4690 (2002), 18-28.
		RVC	M. M. Dhingra, et al., "Polymerization of 1,1,1Trifluoroacetone with Aliphatic Secondary Amines. A Proton and Fluorine Magnetic Resonance Investigation,"Organic Magnetic Resonance, Vol. 9, No. 1 (1977), pp. 23-28.
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		RVC	A. L. Henne, et al., "Trifluoromethylated Butadienes," The Department of Chemistry at The Ohio State University (1954), pp. 5147-5148.
		RVC	K. J. Pryzbilla, et al., "Hexafluoroacetone in Resist Chemistry: A Versatile New Concept for Materials for Deep UV Lithography," SPIE Advances in Resist Chemistry and Process IX Vol. 1672 (1992).
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		RVC	R. R. Dammel, et al., "New Resin Systems for 157 nm Lithography," Journal of Photopolymer Science and Technology, Vol. 14 No. 4 (2001).
		RVC	H. Ito, et al., "Development of 157 nm Positive Resists," J. Vac. Sci. Technol. B 19(6) (2001).
		RVC	H. Ito, "Dissolution Behavior of Chemically Amplified Resist Polymers for 248-, 193-, and 157-nm Lithography," J. Res. & Dev. Vol. 45 No. 5 (2001).
		RVC	S. Cho, et al., "Investigation of a Fluorinated ESCAP based resist for 157 nm Lithography," (2001).
		RVC	K. Patterson, et al., "The Challenges in Materials Design for 157 nm Photoresists," Lithography, Solid State Technology, pp. 41-48 (2000).

EXAMINER R. Kemp	DATE CONSIDERED 4/15/06

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1449 (05/23/06)

PTO/SB/08A (08-03)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known	
Application Number	10/784,377
Filing Date	02/23/2004
First Named Inventor	Richard Van Court Carr, et al.
Art Unit	1752
Examiner Name	
Attorney Docket Number	06425ZP USA

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U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
RVC		US- 2003/059710	03/27/2003	Inoue, Keizo	2003/0059710
		US-			
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] Number[4] Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
RVC		WO 00/67072	11/09/2000	Du Pont		

Examiner Signature	RVC	Date Considered	4/15/06

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